

ZTX796A

PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

Features

- 200 Volt V_{CE0}
- Gain of 250 at $I_C=0.3$ Amps
- Very low saturation voltage

Mechanical Data

- Case: E-Line



Bottom View

E-Line
TO92 Compatible



Pin Configuration

Maximum Ratings

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-200	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Practical Power Dissipation (Note 1)	P_{totp}	1.5	W
Power Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_{tot}	1 5.7	W mW / $^\circ\text{C}$
Thermal Resistance Junction to Ambient ₁ (Note 2)	$R_{\theta JA1}$	175	$^\circ\text{C/W}$
Thermal Resistance Junction to Ambient ₂ (Note 2)	$R_{\theta JA2}$	116	$^\circ\text{C/W}$
Thermal Resistance Junction to Case	$R_{\theta JC}$	70	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +200	$^\circ\text{C}$

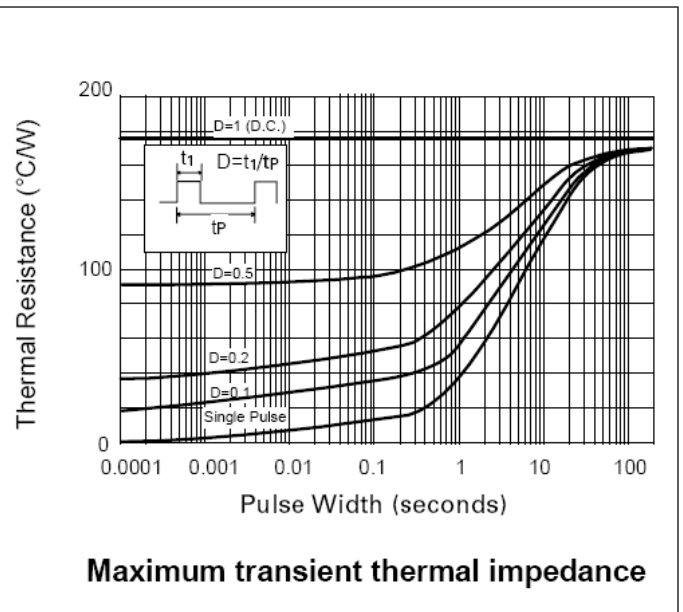
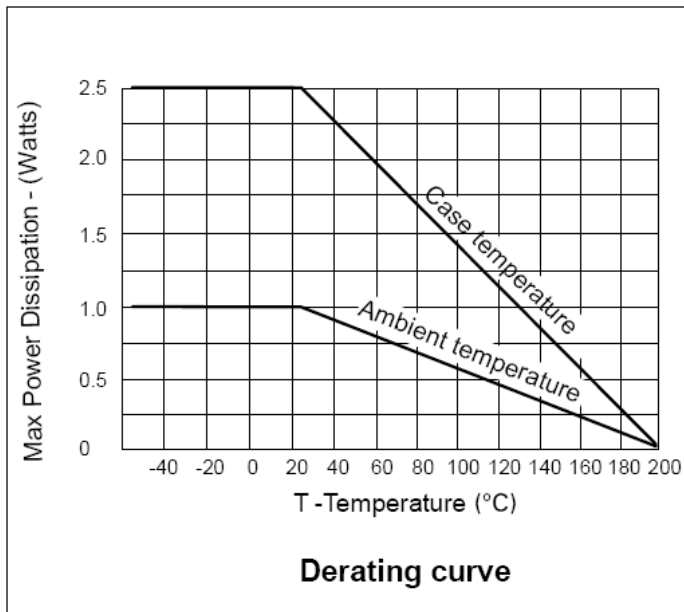
Notes: 1. The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum
2. Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

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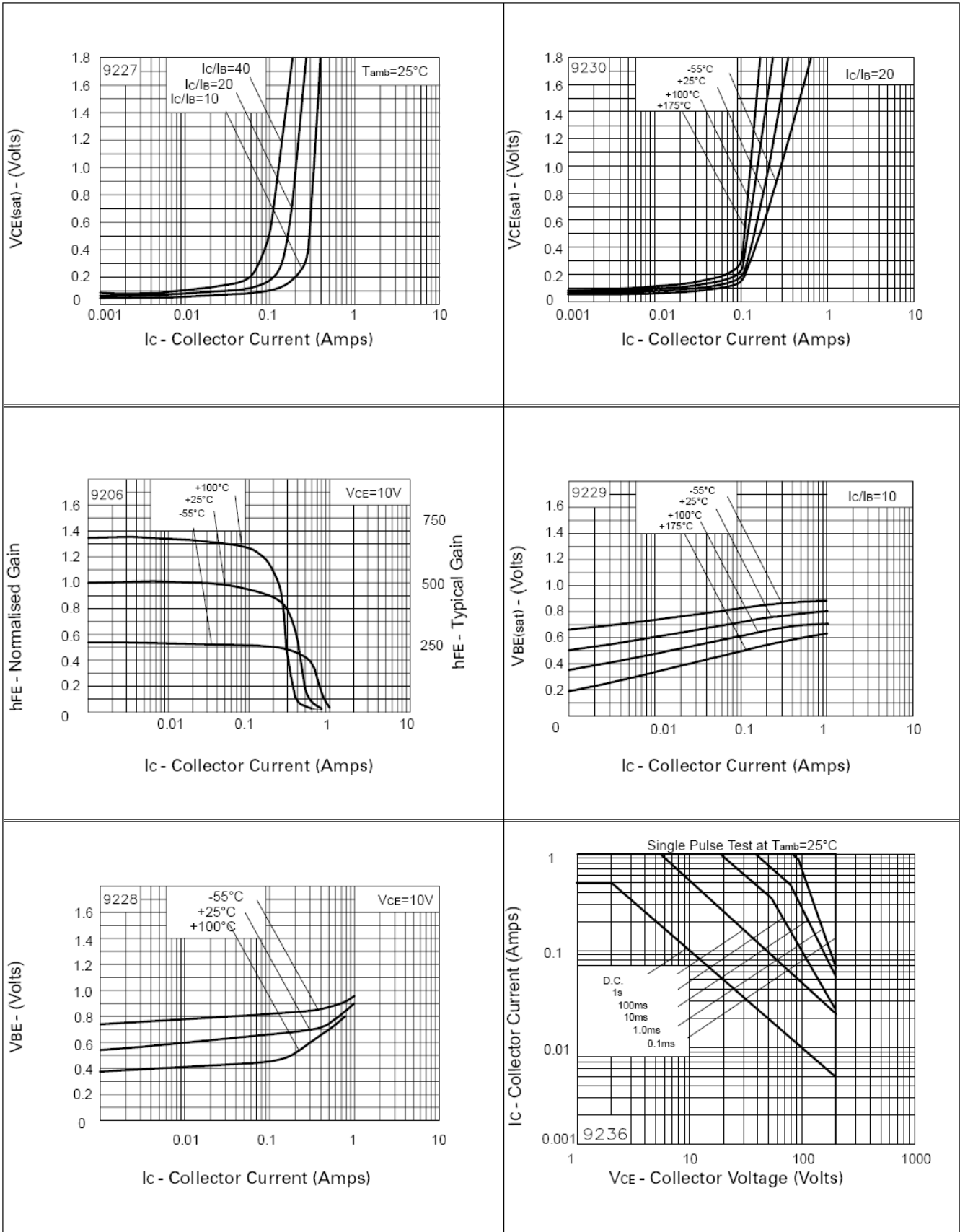
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-200	-	-	V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 3)	$V_{(BR)CEO}$	-200	-	-	V	$I_C = -10\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	-	V	$I_E = -100\mu\text{A}$
Collector Cutoff Current	I_{CBO}	-	-	-0.1	μA	$V_{CB} = -150\text{V}$
Emitter Cutoff Current	I_{EBO}	-	-	-0.1	μA	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage (Note 3)	$V_{CE(sat)}$	-	-	-0.2	mV	$I_C = -50\text{mA}, I_B = -2\text{mA}$
				-0.3	mV	$I_C = -100\text{mA}, I_B = -5\text{mA}$
Base-Emitter Saturation Voltage (Note 3)	$V_{BE(sat)}$	-	-	-0.95	mV	$I_C = -200\text{mA}, I_B = -20\text{mA}$
Base-Emitter Turn-On Voltage (Note 3)	$V_{BE(on)}$	-	-0.67	-	mV	$I_C = -200\text{mA}, V_{CE} = -10\text{V}$
Static Forward Current Transfer Ratio (Note 3)	h_{FE}	300	-	800		$I_C = -10\text{mA}, V_{CE} = -5\text{V}$
						$I_C = -1\text{A}, V_{CE} = -5\text{V}$
						$I_C = -2\text{A}, V_{CE} = -5\text{V}$
						$I_C = -5\text{A}, V_{CE} = -5\text{V}$
Transition Frequency	f_T	100	-	-	MHz	$V_{CE} = -5\text{V}, I_C = -50\text{mA}$ $f = 50\text{MHz}$
Input Capacitance	C_{ibo}	-	225	-	pF	$V_{EB} = -0.5\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{obo}	-	12	-	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Switching Times		-	100	-	ns	$V_{CC} = -50\text{V}, I_C = -100\text{mA}$
						3200

Notes: 3. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$



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